

B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

July 2024 Semester End Main Examinations

Programme: B.E.

Branch: Electrical and Electronics Engineering

Course Code: 22EE5PCPE1

Course: Power Electronics - I

Semester: V

Duration: 3 hrs.

Max Marks: 100

Instructions: 1. Answer any FIVE full questions, choosing one full question from each unit.
2. Missing data, if any, may be suitably assumed.

			UNIT - I			CO	PO	Marks
Important Note: Completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages. Revealing of identification, appeal to evaluator will be treated as malpractice.	1	a)	In a certain application, a power converter of rating 500W with a high efficiency is required. Which power device will you choose for this application if the switching frequency of the devices to be selected as 100kHz. Justify your answer.		CO1	PO1	04	
		b)	What is the importance of knowing the control characteristics of a power device? Plot the control characteristics of thyristor and transistor and list out the differences.		CO1	PO1	08	
		c)	Write a note on intelligent power modules. Draw the functional block diagram of a smart power system		CO1	PO1	08	
			UNIT - II					
	2	a)	What is the significance of reverse recovery time of a power diode? The reverse recovery time of a diode is $t_{rr} = 5 \mu s$, and the rate of fall of the diode current is $di/dt = 80 A/\mu s$. If the softness factor is $SF = 0.5$, determine (a) the storage charge Q_{RR} , and (b) the peak reverse current I_{RR} .		CO2	PO3	06	
		b)	How is a Schottky diode different from a normal diode? How does it operate? Mention the special features of SiC Schottky diodes.		CO2	PO3	06	
		c)	Draw the circuit diagram of a single-phase bridge rectifier that supplies a very high inductive load such as a dc motor. The turns ratio of the transformer is unity. The load is such that the motor draws a ripple-free armature current of I_a . Draw the waveforms of load current and source current. Determine (a) the HF of input current and (b) the input PF of the rectifier.		CO2	PO3	08	
			UNIT - III					
	3	a)	With relevant switching models, plot and discuss the switching characteristics of power BJT.		CO3	PO2	10	
		b)	Draw the structural diagrams of Enhancement type and depletion type MOSFETs. List the major differences between the two types.		CO3	PO2	10	

		Which type of MOSFET is ideal for switching applications? Give reason			
		OR			
4	a)	With switching models and waveforms, explain the dynamic characteristics of MOSFET	CO3	PO2	10
	b)	The bipolar transistor is specified to have β_F in the range of 8 to 40. The load resistance is $R_C = 11 \Omega$. The dc supply voltage is $V_{CC} = 200$ V and the input voltage to the base circuit is $V_B = 10$ V. If $V_{CE(sat)} = 1.0$ V and $V_{BE(sat)} = 1.5$ V, find (a) the value of R_B that results in saturation with an ODF of 5, (b) the β_{forced} .	CO3	PO2	10
		UNIT - IV			
5	a)	What are the advantages of SiC IGBTs over normal Si based IGBTs? Justify your answer with structural diagram of SiC IGBT	CO3	PO2	10
	b)	Why is it important to isolate gate and base drive circuits in a power electronic converter? Discuss any two methods of isolation	CO4	PO2	10
		OR			
6	a)	With a neat cross-sectional diagram discuss the working of IGBT. Plot the static characteristics	CO3	PO2	10
	b)	With relevant circuit diagram, explain the working of the following base control techniques of a transistor. (i) Proportional base control (ii) Antisaturation base control	CO4	PO2	10
		UNIT - V			
7	a)	With the circuit diagram and relevant waveforms, discuss the operation of synchronized UJT firing circuit for firing an SCR.	CO3	PO2	10
	b)	Draw the static characteristics of S. C. R. and explain its different states of operation. Define Holding current and Latching current.	CO2	PO3	10
